CD4011B, CD4012B, CD4023B Types

CMOS NAND GATES

High-Voltage Types (20-Volt Rating)

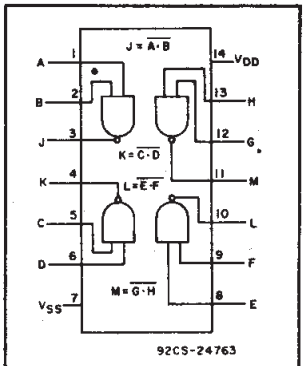
Quad 2 Input – CD4011B
Dual 4 Input – CD4012B
Triple 3 Input – CD4023B

■ CD4011B, CD4012B, and CD4023B NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of CMOS gates. All inputs and outputs are buffered.

The CD4011B, CD4012B, and CD4023B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

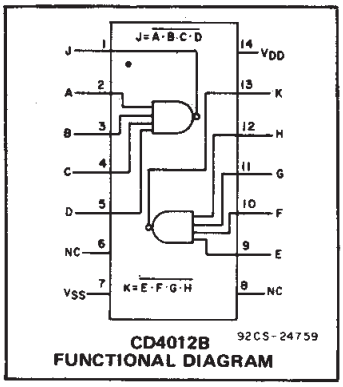
- **Propagation delay time = 60 ns (typ.) at C_L = 50 pF, V_{DD} = 10 V**
- **Buffered inputs and outputs**
- **Standardized symmetrical output characteristics**
- **Maximum input current of 1 μA at 18 V over full package temperature range; 100 nA at 18 V and 25°C**
- **100% tested for quiescent current at 20 V**
- **5-V, 10-V, and 15-V parametric ratings**
- **Noise margin (over full package temperature range:**
  1 V at V_{DD} = 5 V
  2 V at V_{DD} = 10 V
  2.5 V at V_{DD} = 15 V
- **Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of "B" Series CMOS Devices"**



CD4011B
FUNCTIONAL DIAGRAM

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

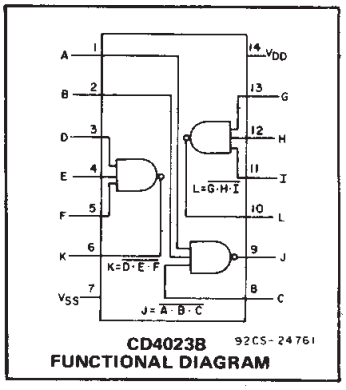


CD4012B
FUNCTIONAL DIAGRAM

RECOMMENDED OPERATING CONDITIONS

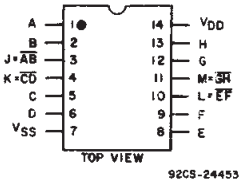
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

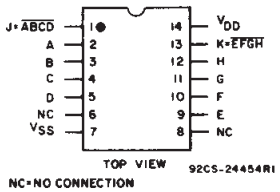


CD4023B
FUNCTIONAL DIAGRAM

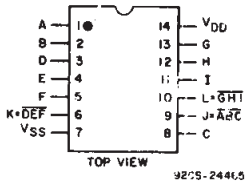
TERMINAL ASSIGNMENTS



CD4011B



NC = NO CONNECTION
CD4012B



CD4023B

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	0.25	0.25	7.5	7.5	–	0.01	0.25	μA
	–	0,10	10	0.5	0.5	15	15	–	0.01	0.5	
	–	0,15	15	1	1	30	30	–	0.01	1	
	–	0,20	20	5	5	150	150	–	0.02	5	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	4.5	–	5	1.5				—	—	1.5	V
	9	–	10	3				—	—	3	
	13.5	–	15	4				—	—	4	
Input High Voltage, V_{IH} Min.	0.5,4.5	–	5	3.5				3.5	—	—	
	1,9	–	10	7				7	—	—	
	1.5,13.5	–	15	11				11	—	—	
Input Current I_{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

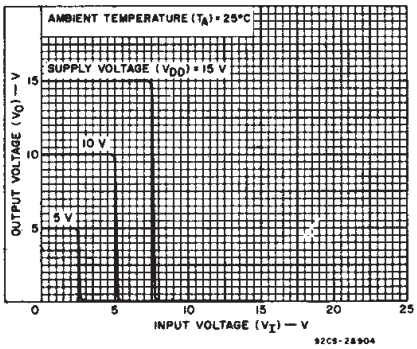


Fig.1 — Typical voltage transfer characteristics.

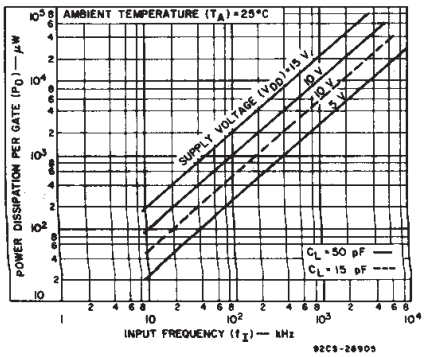


Fig.2 — Typical power dissipation characteristics.

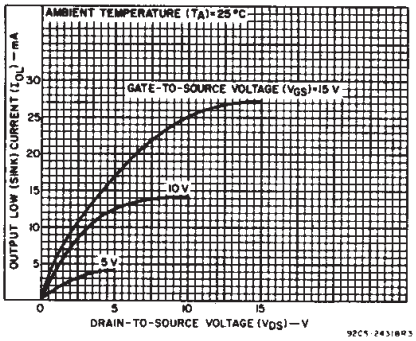


Fig.3 — Typical output low (sink) current characteristics.

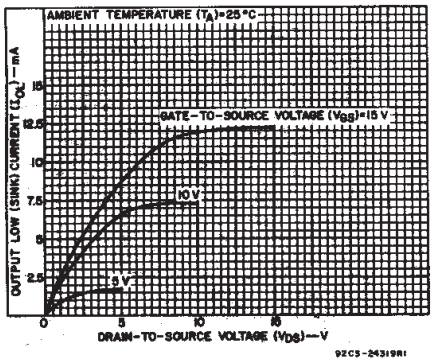


Fig.4 — Minimum output low (sink) current characteristics.

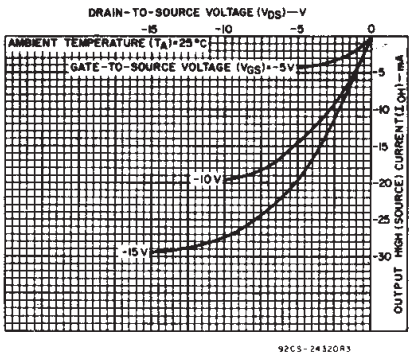


Fig.5 — Typical output high (source) current characteristics.

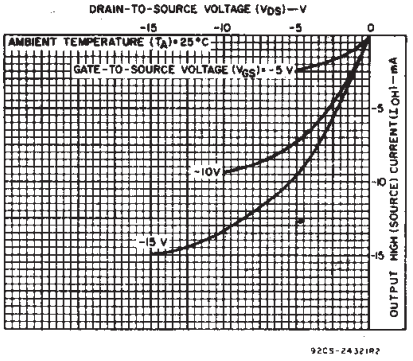


Fig.6 — Minimum output high (source) current characteristics.

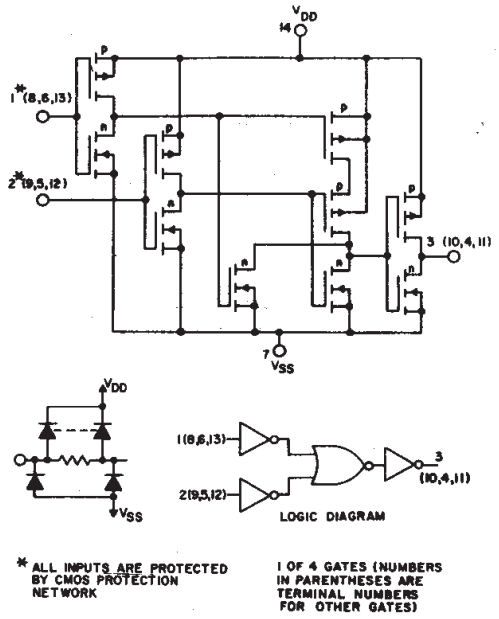


Fig.7 – Schematic and logic diagrams for CD4011B.

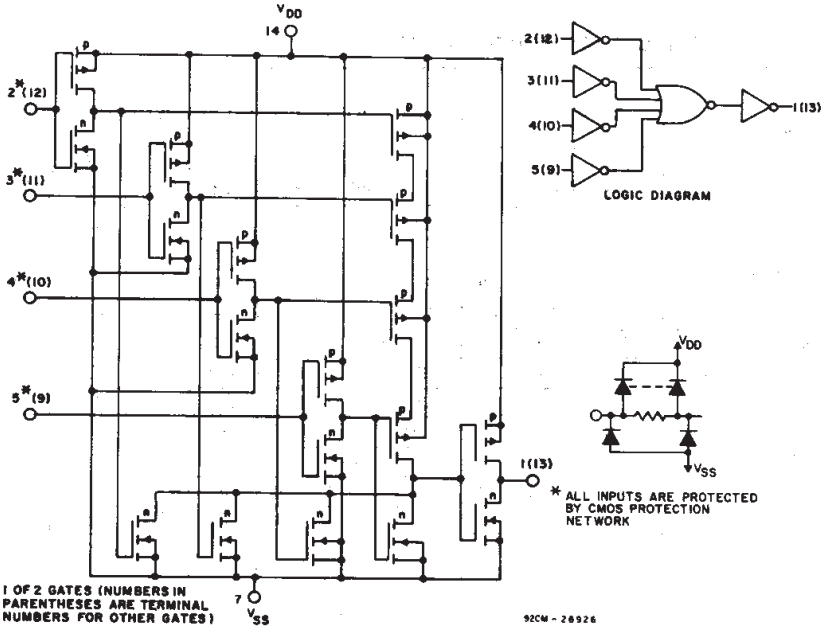


Fig.8 – Schematic and logic diagrams for CD4012B.

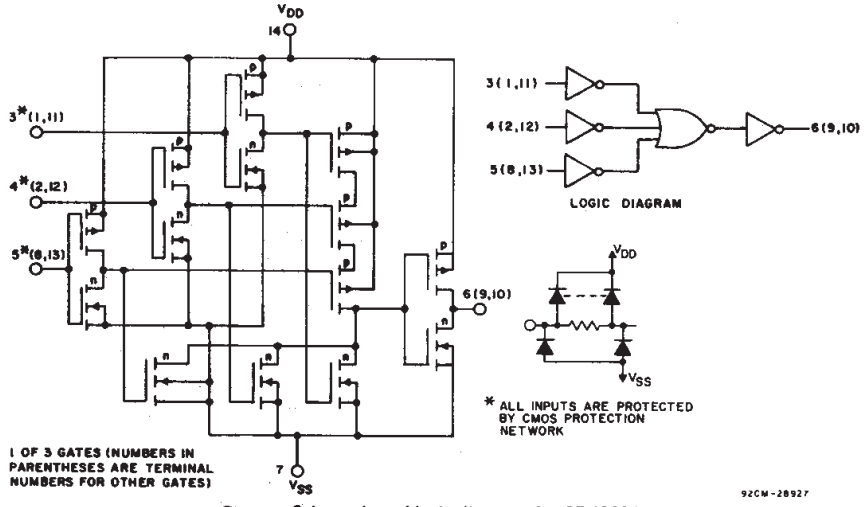


Fig. 9 – Schematic and logic diagrams for CD4023B.

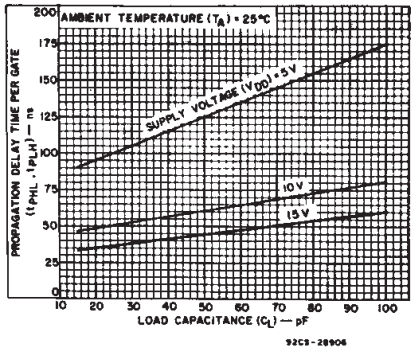


Fig.10 – Typical propagation delay time per gate as a function of load capacitance.

DYNAMIC ELECTRICAL CHARACTERISTICS

At T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200kΩ

CHARACTERISTIC	TEST CONDITIONS		LIMITS		UNITS
		V_{DD} VOLTS	TYP.	MAX.	
Propagation Delay Time, t_{PHL}, t_{PLH}		5	125	250	ns
		10	60	120	
		15	45	90	
Transition Time, t_{THL}, t_{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C_{IN}	Any Input		5	7.5	pF

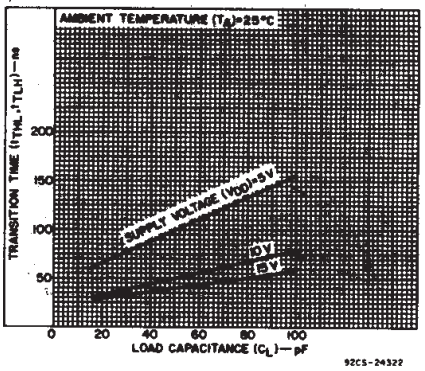


Fig.11 – Typical transition time as a function of load capacitance.

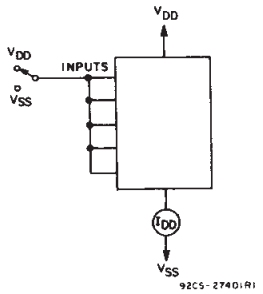


Fig. 12 – Quiescent-device-current test circuit.

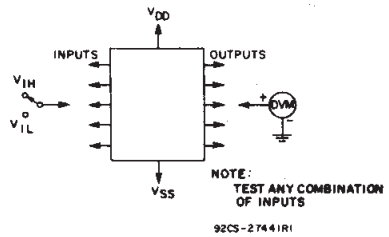


Fig. 13 – Input-voltage test circuit.

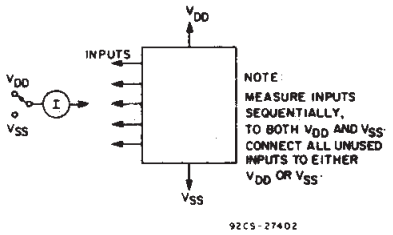
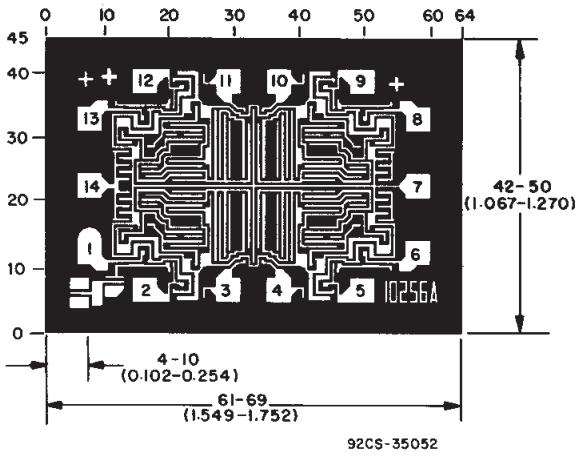
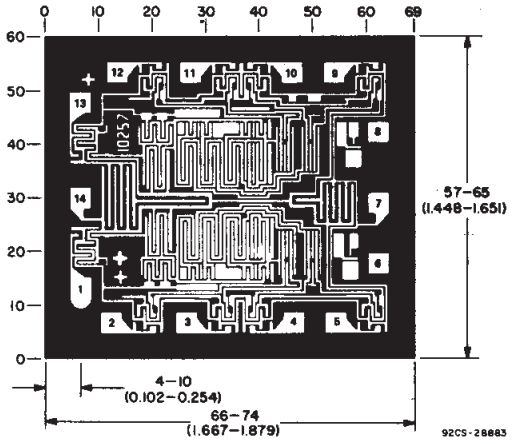


Fig. 14 – Input-current test circuit.

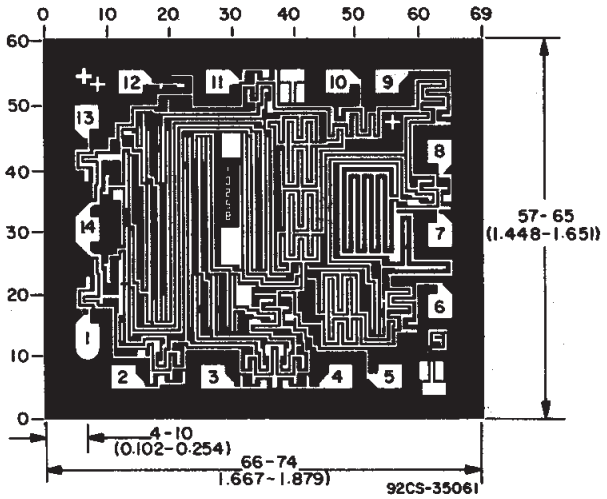
Chip Dimensions and Pad Layouts



CD4011BH



CD4012BH



CD4023BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1999, Texas Instruments Incorporated